



SGS-THOMSON
MICROELECTRONICS

MTV32-400A

(CRT HORIZONTAL DEFLECTION)
MODULATION DIODE

MAIN PRODUCT CHARACTERISTICS

I _F peak	3A
V _{RRM}	400V
t _{rr}	22ns
V _F	1.35V

FEATURES

- PRODUCT SPECIFIC TO HORIZONTAL DEFLECTION
- HIGH REVERSE VOLTAGE
- LOW SWITCHING LOSSES DUE TO SMALL RECOVERY CHARGES

DESCRIPTION

High voltage diode especially designed for horizontal deflection stage in standard and high resolution displays for TV's and monitors.

This device is packaged in DO27A and is intended for use as a MODULATION diode in deflection circuitry with east-west correction.



DO27A
(Plastic)

MTV32-400A

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		400	V
V _{RWM}	Reverse working voltage		400	V
I _F peak	Peak forward current (1)	T _{amb} =130°C (2)	3	A
I _{FRM}	Repetitive peak forward current	tp ≤ 10μs	60	A
I _{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	60	A
T _{stg} T _j	Storage and junction temperature range		- 40 to + 150 - 40 to + 150	°C °C

(1) δ = 0.5 and triangular waveform

(2) on infinite heatsink with 10mm lead length

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction to ambient (*)	20	°C/W

(*) on infinite heatsink with 10mm lead length

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = V _{RWM}	T _j = 25°C			20	µA
			T _j = 100°C			0.5	mA
V _F **	Forward voltage drop	I _F = 3 A	T _j = 25°C			1.45	V
			T _j = 100°C			1.35	

Pulse test : * t_p = 5 ms, duty cycle < 2 %** t_p = 380 µs, duty cycle < 2 %

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
t _{rr}	Reverse recovery time	I _F = 0.5 A I _{rr} = 0.25 A	I _R = 1 A T _j = 25°C			22	ns

TURN ON SWITCHING

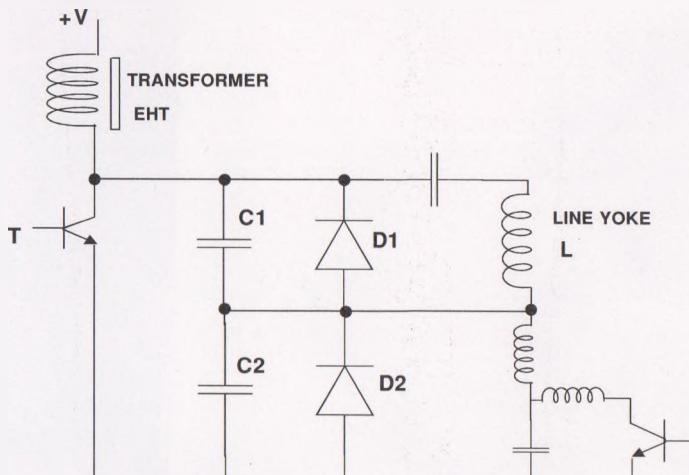
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
t _{FR}	Forward recovery time	I _F = 3 A dI _F /dt = 100 A/µs Mesured at 1.1 x V _F T _j = 25°C				0.1	µs
V _{FP}						17	V

To evaluate the conduction losses, in case of triangular current, use the following equation :

$$P = \frac{1.17 \times I_P \times \delta}{2} + \frac{0.06 \times I_P^2 \times \delta}{3}$$

 δ : duty cycleI_P : Peak currentfor I_P = 3A and δ = 0.5, P = 0.97 W

BASIC E-W DIODE MODULATOR CIRCUIT



D1=DTV32-1000A D2=MTV32-400A